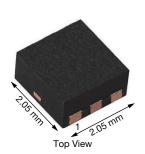


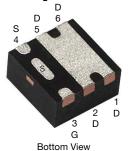
Vishay Siliconix

N-Channel 30 V (D-S) MOSFET

| PRODUCT SUMMARY | | | | | | | | | |
|---------------------|-----------------------------------|-------------------------|-----------------------|--|--|--|--|--|--|
| V _{DS} (V) | $R_{DS(on)}$ (Ω) | I _D (A) b, c | Q _g (TYP.) | | | | | | |
| 30 | 0.0200 at V _{GS} = 10 V | 10.1 | 5.6 | | | | | | |
| | 0.0240 at V _{GS} = 4.5 V | 9.2 | 5.0 | | | | | | |

PowerPAK® SC-70-6L Single



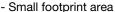


Marking Code: A L
Ordering Information:

SiA432DJ-T1-GE3 (Lead (Pb)-free and Halogen-free) SiA432DJ-T4-GE3 (Lead (Pb)-free and Halogen-free)

FEATURES

- TrenchFET® power MOSFET
- Thermally enhanced PowerPAK® SC-70 package

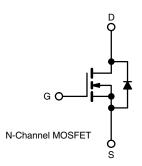




- 100 % UIS tested
- Material categorization:
 For definitions of compliance please see www.vishay.com/doc?99912

APPLICATIONS

Load Switch



| PARAMETER | | SYMBOL | LIMIT | V | |
|--|-----------------------------------|-----------------|----------------------|----|--|
| Drain-Source Voltage | | V _{DS} | 30 | | |
| Gate-Source Voltage | | V _{GS} | ± 20 | | |
| | T _C = 25 °C | | 12 ^a | | |
| O | T _C = 70 °C | | 12 ^a | | |
| Continuous Drain Current (T _J = 150 °C) | T _A = 25 °C | I _D | 10.1 ^{b, c} | | |
| | T _A = 70 °C | | 8.1 ^{b, c} | | |
| Pulsed Drain Current | | I _{DM} | 30 | A | |
| Osadia a a Osaga Basis Bisada Osaga | T _C = 25 °C | | 12 ^a | | |
| Continuous Source-Drain Diode Current | T _A = 25 °C | I _S | 2.9 b, c | | |
| Single-Pulse Avalanche Current | L = 0.1 mH | I _{AS} | 15.5 | | |
| Single-Pulse Avalanche Energy | L = 0.1 IIIH | E _{AS} | 12 | mJ | |
| | T _C = 25 °C | | 19.2 | | |
| Maximum Dawar Dissination | T _C = 70 °C | В | 12.3 | w | |
| Maximum Power Dissipation | T _A = 25 °C | P _D | 3.5 b, c | VV | |
| | T _A = 70 °C | | 2.2 b, c | | |
| Operating Junction and Storage Temperatur | T _J , T _{stg} | -55 to 150 | 00 | | |
| Soldering Recommendations (Peak Tempera | | 260 | °C | | |

| THERMAL RESISTANCE RATINGS | | | | | | | | | |
|------------------------------------|--------------|-------------------|---------|---------|--------|--|--|--|--|
| PARAMETER | | SYMBOL | TYPICAL | MAXIMUM | UNIT | | | | |
| Maximum Junction-to-Ambient b, f t | | R_{thJA} | 28 | 36 | °C/W | | | | |
| Maximum Junction-to-Case (Drain) | Steady State | R _{thJC} | 5.3 | 6.5 | 7 0/00 | | | | |

Notes

- a. Package limited.
- b. Surface mounted on 1" x 1" FR4 board.
- c. t = 5 s
- d. See solder profile (<u>www.vishay.com/doc?73257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- e. Rework conditions: Manual soldering with a soldering iron is not recommended for leadless components.
- f. Maximum under steady state conditions is 80 °C/W.

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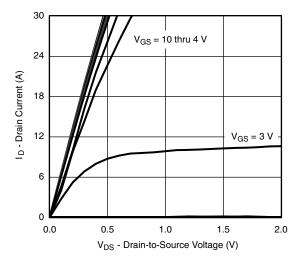
| SPECIFICATIONS (T _J = 25 °C, u | SYMBOL | TEST CONDITIONS | MIN. | TYP. | MAX. | UNIT |
|--|--------------------------------------|---|---------|--------|--------|-------|
| Static | STINIBOL | TEST CONDITIONS | IVIIIV. | 1117. | WAA. | ONIT |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = 250 μA | 30 | _ | _ | V |
| V _{DS} Temperature Coefficient | ΔV _{DS} /T _J | 100 01,10 200 p | - | 35 | _ | mV/°C |
| V _{GS(th)} Temperature Coefficient | ΔV _{GS(th)} /T _J | I _D = 250 μA | _ | -5.6 | _ | |
| Gate-Source Threshold Voltage | V _{GS(th)} | $V_{DS} = V_{GS}$, $I_D = 250 \mu A$ | 1 | - | 3 | V |
| Gate-Source Leakage | I _{GSS} | $V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$ | - | _ | ± 100 | nA |
| data data da Latinaga | 1033 | V _{DS} = 30 V, V _{GS} = 0 V | _ | _ | 1 | μA |
| Zero Gate Voltage Drain Current | I _{DSS} | $V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 \text{ °C}$ | _ | - | 10 | |
| On-State Drain Current ^a | I _{D(on)} | $V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$ | 20 | - | - | Α |
| | B(GII) | V _{GS} = 10 V, I _D = 6 A | - | 0.0158 | 0.0200 | |
| Drain-Source On-State Resistance a | R _{DS(on)} | V _{GS} = 4.5 V, I _D = 5 A | - | 0.0190 | 0.0240 | Ω |
| Forward Transconductance a | 9 _{fs} | V _{DS} = 10 V, I _D = 6 A | - | 22 | - | S |
| Dynamic ^b | G.S | | | | | |
| Input Capacitance | C _{iss} | | - | 800 | - | pF |
| Output Capacitance | Coss | V _{DS} = 15 V, V _{GS} = 0 V, f = 1 MHz | - | 115 | - | |
| Reverse Transfer Capacitance | C _{rss} | | - | 54 | - | |
| T | Qg | V _{DS} = 15 V, V _{GS} = 10 V, I _D = 10 A | - | 13 | 20 | nC |
| Total Gate Charge | | | - | 5.6 | 9 | |
| Gate-Source Charge | Q _{gs} | $V_{DS} = 15 \text{ V}, V_{GS} = 4.5 \text{ V}, I_{D} = 10 \text{ A}$ | - | 2 | - | |
| Gate-Drain Charge | Q_{gd} | | - | 1.4 | - | |
| Gate Resistance | R _g | f = 1 MHz | - | 3 | - | Ω |
| Turn-On Delay Time | t _{d(on)} | | - | 15 | 25 | |
| Rise Time | t _r | $V_{DD} = 15 \text{ V}, R_{L} = 1.9 \Omega$ | - | 11 | 17 | ns |
| Turn-Off Delay Time | t _{d(off)} | $I_D \cong 8 \text{ A}, V_{GEN} = 4.5 \text{ V}, R_g = 1 \Omega$ | - | 15 | 25 | |
| Fall Time | t _f | | - | 10 | 15 | |
| Turn-On Delay Time | t _{d(on)} | | - | 8 | 15 | |
| Rise Time | t _r | $V_{DD} = 15 \text{ V}, R_{L} = 1.9 \Omega$ | - | 8 | 15 | |
| Turn-Off Delay Time | t _{d(off)} | $I_D \cong 8 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$ | - | 15 | 25 | |
| Fall Time | all Time t _f | | - | 8 | 15 | |
| Drain-Source Body Diode Characteristic | s | | | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | - | - | 12 | Δ |
| Pulse Diode Forward Current | ode Forward Current I _{SM} | | - | - | 30 | А |
| Body Diode Voltage | Diode Voltage V _{SD} | | - | 0.8 | 1.2 | V |
| Body Diode Reverse Recovery Time | t _{rr} | | | 16 | 30 | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | I _F = 8 A, dl/dt = 100 A/μs, T _J = 25 °C | - | 8 | 15 | nC |
| Reverse Recovery Fall Time | ta | i _f = 0 A, αί/αι = 100 Α/μs, 1 _J = 25 °C | - | 9.8 | - | ne |
| Reverse Recovery Rise Time | t _b | | - | 6.2 | - | ns |

Notes

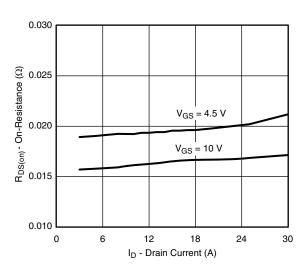
- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

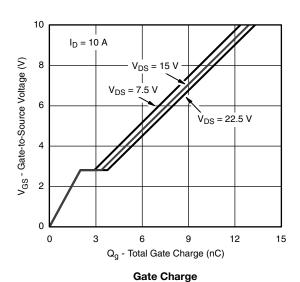




Output Characteristics



On-Resistance vs. Drain Current and Gate Voltage



T_C = 25 °C

T_C = 25 °C

T_C = -55 °C

1.0

1.5

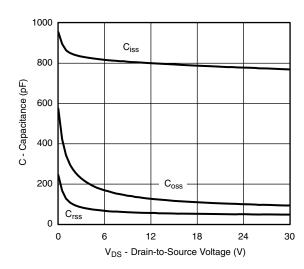
2.0

2.5

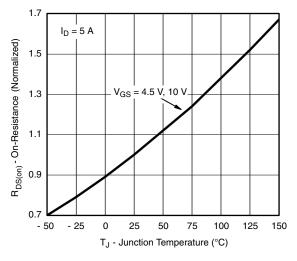
3.0

V_{GS} - Gate-to-Source Voltage (V)

Transfer Characteristics

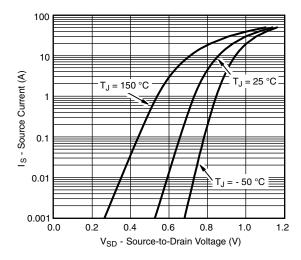


Capacitance

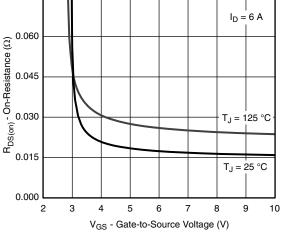


On-Resistance vs. Junction Temperature

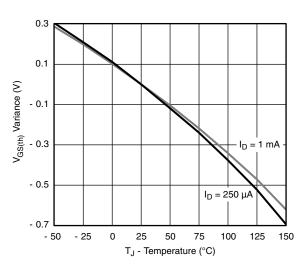




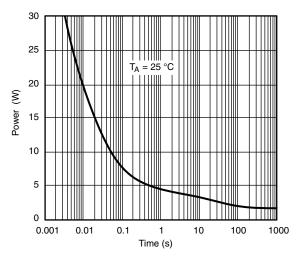
Source-Drain Diode Forward Voltage



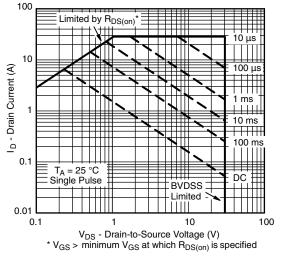
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage

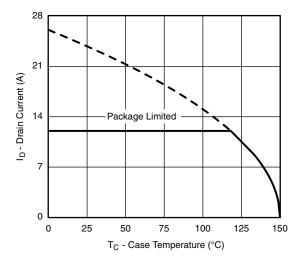


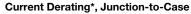
Single Pulse Power (Junction-to-Ambient)

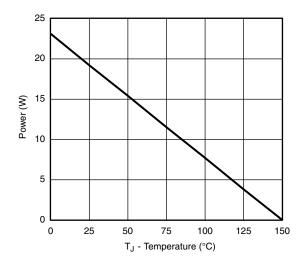


Safe Operating Area, Junction-to-Ambient





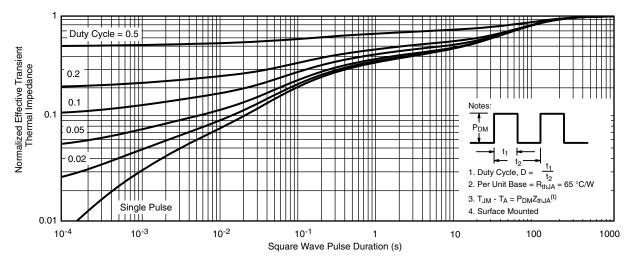




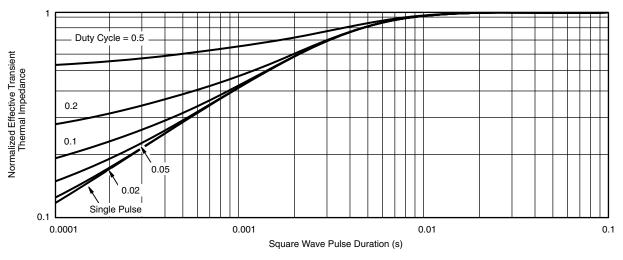
Power Derating

^{*} The power dissipation P_D is based on T_{J (max.)} = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.





Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

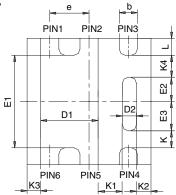
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?68697.





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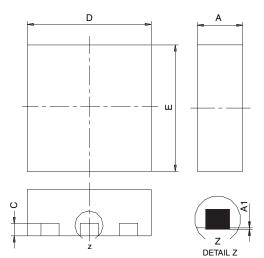
PowerPAK® SC70-6L





BACKSIDE VIEW OF SINGLE

BACKSIDE VIEW OF DUAL



- All dimensions are in millimeters
 Package outline exclusive of mold flash and metal burr
 Package outline inclusive of plating

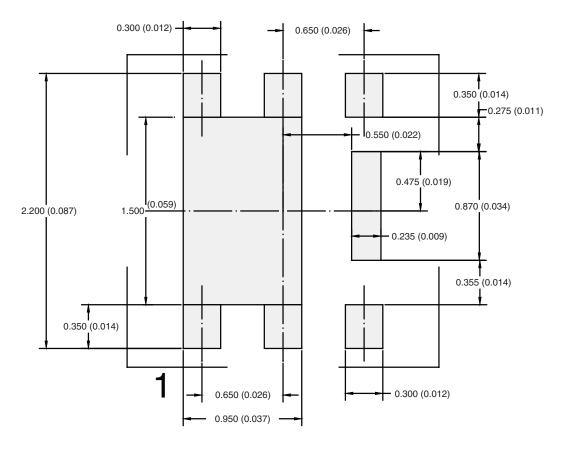
| | SINGLE PAD | | | | | | DUAL PAD | | | | | | |
|--------------------------------|-------------|-----------|-------|-----------|-----------|-------|-------------|-----------|-----------|-----------|-----------|-------|--|
| DIM | MILLIMETERS | | | INCHES | | | MILLIMETERS | | | INCHES | | | |
| | Min | Nom | Max | Min | Nom | Max | Min | Nom | Max | Min | Nom | Max | |
| Α | 0.675 | 0.75 | 0.80 | 0.027 | 0.030 | 0.032 | 0.675 | 0.75 | 0.80 | 0.027 | 0.030 | 0.032 | |
| A 1 | 0 | - | 0.05 | 0 | - | 0.002 | 0 | - | 0.05 | 0 | - | 0.002 | |
| b | 0.23 | 0.30 | 0.38 | 0.009 | 0.012 | 0.015 | 0.23 | 0.30 | 0.38 | 0.009 | 0.012 | 0.015 | |
| С | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | 0.15 | 0.20 | 0.25 | 0.006 | 0.008 | 0.010 | |
| D | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | |
| D1 | 0.85 | 0.95 | 1.05 | 0.033 | 0.037 | 0.041 | 0.513 | 0.613 | 0.713 | 0.020 | 0.024 | 0.028 | |
| D2 | 0.135 | 0.235 | 0.335 | 0.005 | 0.009 | 0.013 | | | | | | | |
| E | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | 1.98 | 2.05 | 2.15 | 0.078 | 0.081 | 0.085 | |
| E1 | 1.40 | 1.50 | 1.60 | 0.055 | 0.059 | 0.063 | 0.85 | 0.95 | 1.05 | 0.033 | 0.037 | 0.041 | |
| E2 | 0.345 | 0.395 | 0.445 | 0.014 | 0.016 | 0.018 | | | | | | | |
| E3 | 0.425 | 0.475 | 0.525 | 0.017 | 0.019 | 0.021 | | | | | | | |
| е | | 0.65 BSC | | | 0.026 BSC | ; | 0.65 BSC | | | 0.026 BSC | | | |
| K | | 0.275 TYP | ١ | | 0.011 TYP | | 0.275 TYP | | | 0.011 TYP | | | |
| K1 | | 0.400 TYP | ١ | | 0.016 TYP | | | 0.320 TYP | | | 0.013 TYP | | |
| K2 | | 0.240 TYP | ١ | 0.009 TYP | | | 0.252 TYP | | 0.010 TYP | | | | |
| К3 | | 0.225 TYP | 1 | 0.009 TYP | | | | | | | | | |
| K4 | | 0.355 TYP | | 0.014 TYP | | | | | | | | | |
| L | 0.175 | 0.275 | 0.375 | 0.007 | 0.011 | 0.015 | 0.175 | 0.275 | 0.375 | 0.007 | 0.011 | 0.015 | |
| Т | | | | | | | 0.05 | 0.10 | 0.15 | 0.002 | 0.004 | 0.006 | |
| FCN: C-07431 – Bey C 06-Aug-07 | | | | | | | | | | | | | |

DWG: 5934

Document Number: 73001 06-Aug-07



RECOMMENDED PAD LAYOUT FOR PowerPAK® SC70-6L Single



Dimensions in mm/(Inches)

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ATTLICATION NOT



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